



## 1-Line Bidirectional ESD Protection Diode

### General description

Low capacitance bidirectional ElectroStatic Discharge (ESD) protection diode in a DFN1006(SOD882) leadless ultra small Surface-Mounted Device (SMD) plastic package designed to protect one signal line from the damage caused by ESD and other transients.

### Features and benefits

- . Low Capacitance 2.5 pF(Typ)
- . Reverse stand-off voltage: 5V Max
- . Low leakage current: nA Level
- . Response time is typically < 1 ns
- . IEC61000-4-2 Level 4 ESD Protection

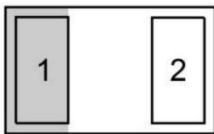
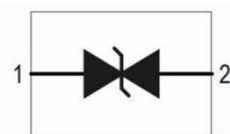
### Application information

- . Cellular Handsets & Accessories
- . Digital Cameras
- . Peripherals
- . Keypads, Side Keys, USB 2.0, LCD Displays
- . MP3 Players
- . Portable Instrumentation
- . Notebooks & Desktop Computers

### Ordering information

Device	Package	Marking	Packaging
ESD8LM5.0C	DFN1006-2L	VB	10000/Tape & Reel

### Schematic & Pin configuration

Simplified outline	Graphic symbol
	

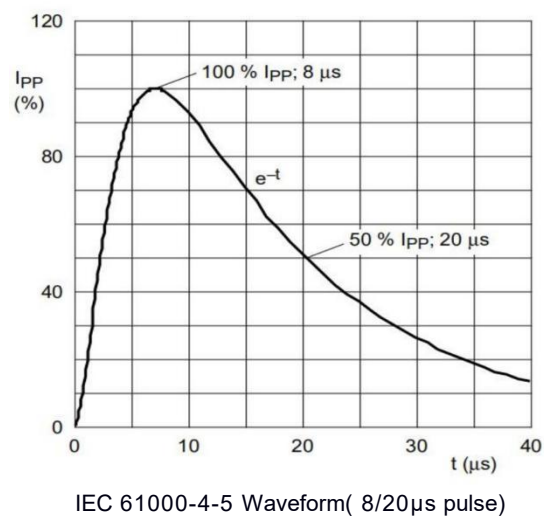
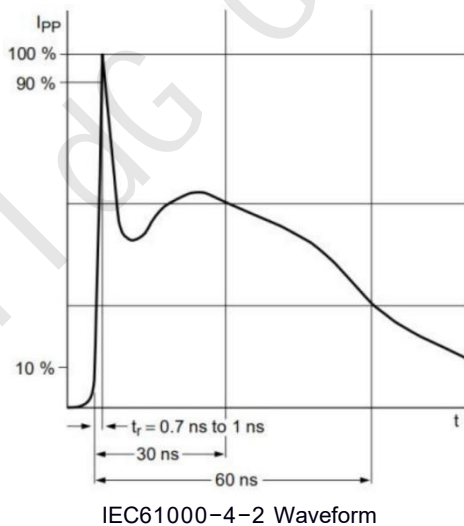
**Maximum Ratings** ( $T_{OP} = 25 \text{ } ^\circ\text{C}$ , unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power ( $T_p = 8/20 \text{ } \mu\text{s}$ )	$P_{PPM}$	30	W
Rated Peak Pulse Current ( $T_p = 8/20 \text{ } \mu\text{s}$ )	$I_{PPM}$	2.5	A
ESD voltage IEC 61000-4-2 (air discharge)	$V_{ESD}$	15	kV
ESD voltage IEC 61000-4-2 (contact discharge)	$V_{ESD}$	8	kV
Maximum lead temperature for soldering during 10s	$T_L$	260	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Operating Temperature Range	$T_{OP}$	-40 to +125	$^\circ\text{C}$
Maximum junction temperature	$T_j$	150	$^\circ\text{C}$

**Electrical Characteristics** ( $T_{OP} = 25 \text{ } ^\circ\text{C}$ , unless otherwise specified)

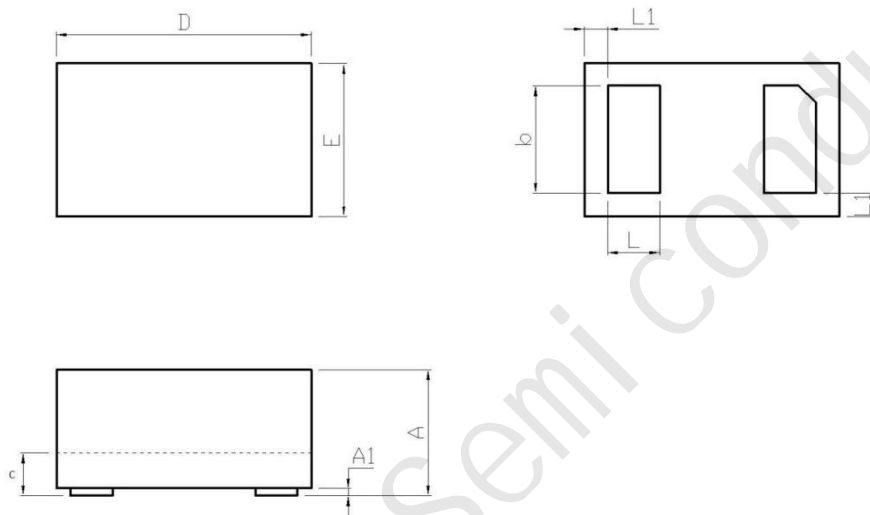
Parameter	Symbol	Min	Typ	Max	Unit	Condition
Reverse Working Voltage	$V_{RWM}$	--	--	5.0	V	
Breakdown Voltage	$V_{BR}$	6.0	--	9.0	V	$I_T = 1\text{mA}$
Leakage Current $I_{Leak}$	$I_R$	--	--	100	nA	$V_{RWM} = 5\text{V}$
Clamping Voltage	$V_C$	--	--	12.0	V	$I_{PP} = 2\text{A}, T_p = 8/20\mu\text{s}$
Junction Capacitance	$C_j$	--	2.5	3.2	pF	$V_R = 0\text{V}, f = 1\text{MHz}$

**Typical Electrical and Thermal Characteristics (Curves)**



**Package Outline Dimensions**

**DFN1006-2L**



DFN1006-2L (mm)			
Dim	Min	Typ.	Max
A	0.46	0.48	0.50
A1	0	0.02	0.05
b	0.45	0.5	0.55
c	0.1	0.12	0.14
D	0.95	1.00	1.05
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.035	0.05	0.065
h	0.07	0.12	0.17